Device fabrication progress on epitaxial graphene on SiC

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Epitaxial graphene on SiC has been demonstrated to be a viable route toward
electronic device fabrication. While a top gate is required to locally change
doping density and carrier type, specifically for field effect transistors graphene
devices, back gating is relevant to globally change carrier and to address the
graphene layer at the SiC-graphene interface. Here we report result on back-gating
and top-gating epitaxial graphene grown on SiC by the confinement controlled
sublimation method. Post-patterning treatments of graphene devices are also
discussed.

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